**ON Semiconductor** 

Is Now

# Onsemi

To learn more about onsemi<sup>™</sup>, please visit our website at <u>www.onsemi.com</u>

onsemi and ONSEMI: and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product factures, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application is the human body. Should Buyer purchase or use onsemi products for any such unintended or unauthorized application, Buyer shall indemnify and hold onsemi and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application, Buyer shall indemnify and hold ons

# Silicon Carbide Schottky Diode

650 V, 10 A

# FFSM1065B

#### Description

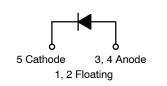
Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost. **Features** 



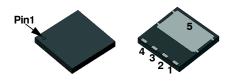
# **ON Semiconductor®**

#### www.onsemi.com

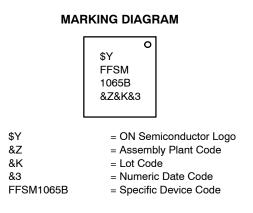
V <sub>RRM</sub>	IF
650 V	10 A



Schottky Diode



PQFN 8×8, 2P CASE 483AP



#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 2 of this data sheet.

# • Max Junction Temperature 175°C

- Avalanche Rated 49 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### Applications

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

#### MAXIMUM RATINGS (T<sub>C</sub> = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit	
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	650	V	
Single Pulse Avalanche Energy (s $25^{\circ}\text{C},\text{I}_{\text{AS}}$ = 14 A, L = 0.5 mH, V =	E <sub>AS</sub>	49	mJ	
Continuous Rectified Forward Current	T <sub>C</sub> < 150	١ <sub>F</sub>	10	А
Current	T <sub>C</sub> < 135		13.5	
Non-Repetitive Peak Forward	T <sub>C</sub> = 25°C	I <sub>FM</sub>	532	А
Surge Current (t <sub>P</sub> = 10 $\mu$ s)	T <sub>C</sub> = 150°C		468	
Non-Repetitive Forward Surge Current (Half-Sine Pulse)	T <sub>C</sub> = 25°C t <sub>P</sub> = 8.3 ms	I <sub>FSM</sub>	42	A
Power Dissipation	T <sub>C</sub> = 25°C	P <sub>tot</sub>	98	W
	T <sub>C</sub> = 150°C	]	16	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	–55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL RESISTANCE

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case, Max	$R_{\theta JC}$	1.53	°C/W

© Semiconductor Components Industries, LLC, 2019

July, 2020 - Rev. 2

# **ELECTRICAL CHARACTERISTICS** ( $T_J = 25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
V <sub>F</sub>	Forward Voltage	I <sub>F</sub> = 10 A, T <sub>J</sub> = 25°C	-	1.38	1.7	V
		I <sub>F</sub> = 10 A, T <sub>J</sub> = 125°C	-	1.6		
		I <sub>F</sub> = 10 A, T <sub>J</sub> = 150°C	-	1.67		
I <sub>R</sub>	Reverse Current	$V_{\rm R}$ = 650 V, T <sub>J</sub> = 25°C	-	0.5	40	μΑ
		$V_{\rm R}$ = 650 V, T <sub>J</sub> = 125°C	-	1	80	
		$V_{\rm R}$ = 650 V, T <sub>J</sub> = 175°C	-	2	160	
$Q_{C}$	Total Capacitive Charge	V = 400 V	-	25	-	nC
С	Total Capacitance	V <sub>R</sub> = 1 V, f = 100 kHz	-	424	-	pF
		V <sub>R</sub> = 300 V, f = 100 kHz	-	39	-	1
		V <sub>R</sub> = 600 V, f = 100 kHz	-	35	-	1

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

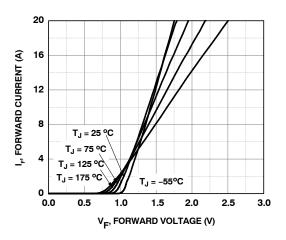
#### **ORDERING INFORMATION**

Part Number	Top Marking	Package	Shipping*
FFSM1065B	FFSM1065B	PQFN 8X8, 2P (Halogen Free)	3000 Units / Tape & Reel

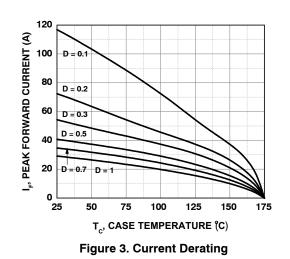
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D

#### **TYPICAL CHARACTERISTICS**

(T<sub>J</sub> = 25°C unless otherwise noted)



**Figure 1. Forward Characteristics** 



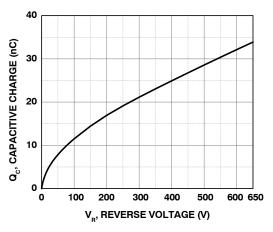
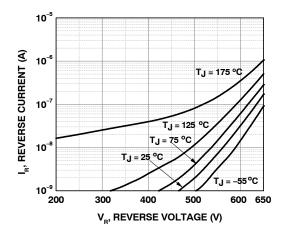


Figure 5. Capacitive Charge vs. Reverse Voltage



**Figure 2. Reverse Characteristics** 

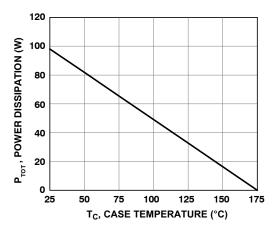


Figure 4. Power Derating

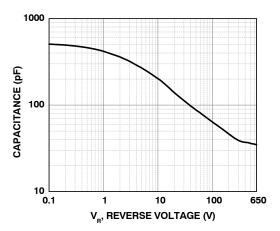


Figure 6. Capacitance vs. Reverse Voltage

## TYPICAL CHARACTERISTICS (continued)

(T<sub>J</sub> =  $25^{\circ}C$  unless otherwise noted)

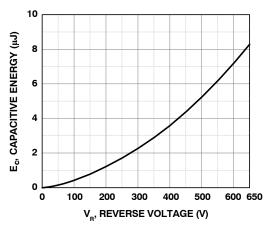


Figure 7. Capacitance Stored Energy

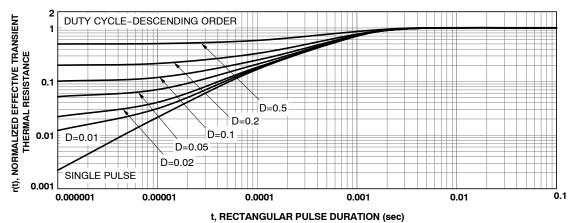
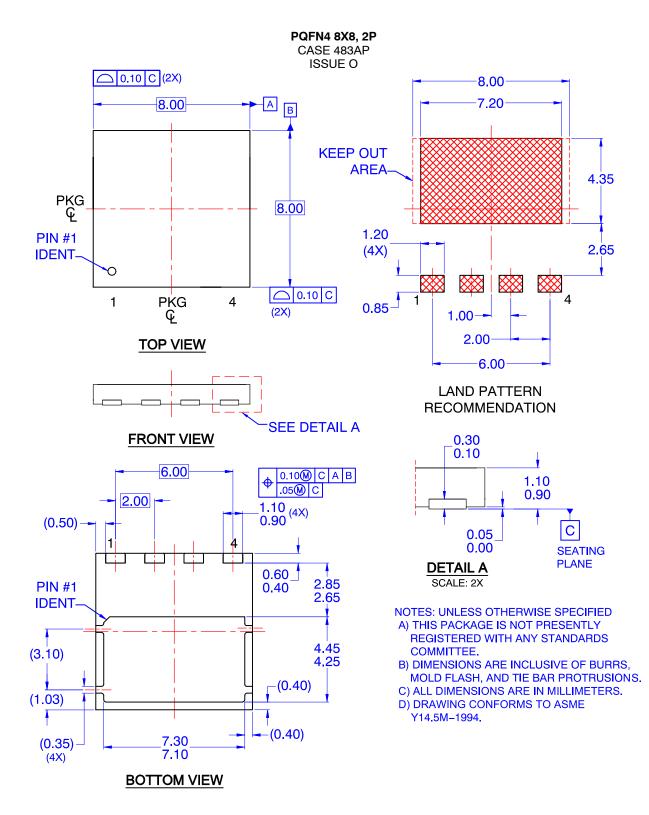


Figure 8. Junction-to-Case Transient Thermal Response Curve

#### PACKAGE DIMENSIONS



ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, and listributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such

# PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT: Email Requests to: orderlit@onsemi.com

#### TECHNICAL SUPPORT

ON Semiconductor Website: www.onsemi.com

North American Technical Support: Voice Mail: 1 800–282–9855 Toll Free USA/Canada Phone: 011 421 33 790 2910 Europe, Middle East and Africa Technical Support: Phone: 00421 33 790 2910 For additional information, please contact your local Sales Representative

٥